

# SJPM-H4

**PRV : 400 Volts**  
**I<sub>o</sub> : 2.0 Ampere**

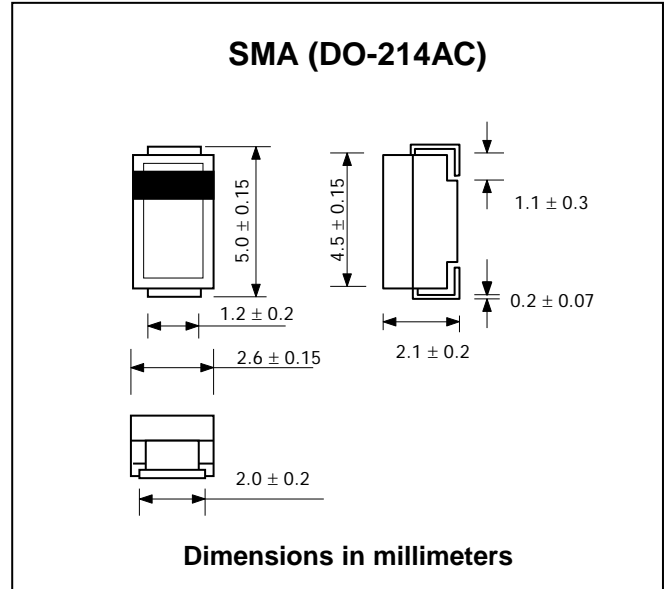
**FEATURES :**

- \* Glass passivated junction chip
- \* High current capability
- \* High reliability
- \* Low reverse current
- \* Low forward voltage drop
- \* Pb / RoHS Free

**MECHANICAL DATA :**

- \* Case : SMA Molded plastic
- \* Epoxy : UL94V-0 rate flame retardant
- \* Lead : Lead Formed for Surface Mount
- \* Polarity : Color band denotes cathode end
- \* Mounting position : Any
- \* Weight : 0.064 gram

## GLASS PASSIVATED JUNCTION SILICON SURFACE MOUNT



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.  
 Single phase, half wave, 60 Hz, resistive or inductive load.  
 For capacitive load, derate current by 20%.

RATING	SYMBOL	VALUE	UNIT
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	400	V
Maximum Peak Reverse Surge Voltage	V <sub>RSM</sub>	400	V
Maximum Average Forward Current	I <sub>F(AV)</sub>	2.0	A
Maximum Peak Forward Surge Current, Half-cycle Sinewave Single Shot, 50 Hz	I <sub>FSM</sub>	45	A
Maximum Forward Voltage at I <sub>F</sub> = 2.0 A	V <sub>F</sub>	1.1	V
Maximum Reverse Current at V <sub>R</sub> = V <sub>RRM</sub> T <sub>j</sub> = 25 °C	I <sub>R</sub>	10	μA
Maximum Reverse Current at V <sub>R</sub> = V <sub>RRM</sub> T <sub>j</sub> = 150 °C	I <sub>R(H)</sub>	50	μA
Thermal Resistance, Junction to Lead	R <sub>θJL</sub>	20	°C/W
Junction Temperature Range	T <sub>J</sub>	- 40 to + 150	°C
Storage Temperature Range	T <sub>STG</sub>	- 40 to + 150	°C

RATING AND CHARACTERISTIC CURVES ( SJPM-H4 )

FIG.1 - CURRENT DERATING, LEAD

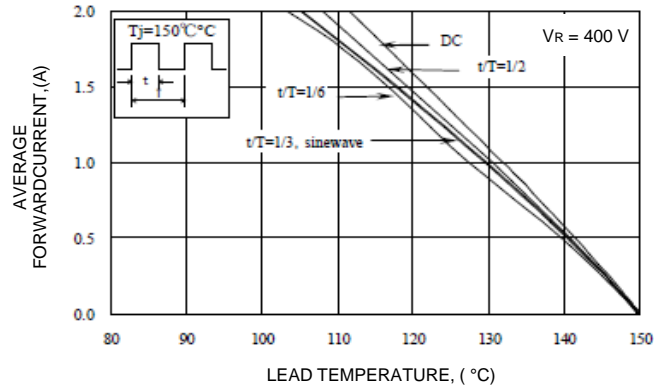


FIG.2 - MAXIMUM STEADY STATE POWER DISSIPATION AS A FUNCTION OF AVERAGE FORWARD CURRENT

